

Integrated Circuit Packaging and Thermal Design

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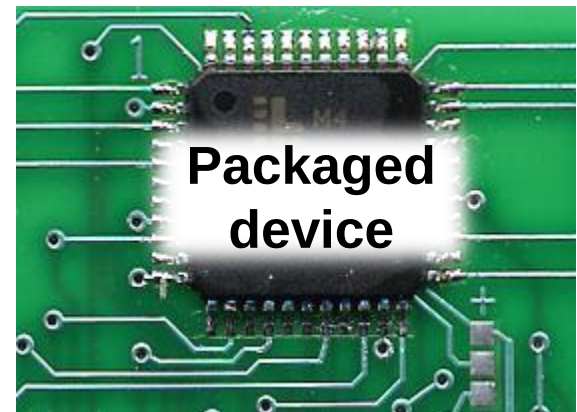
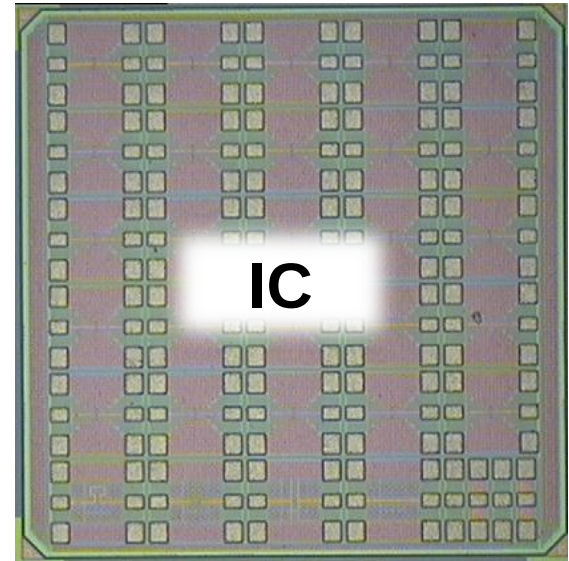
Introduction to IC Technologies

Packaging

- Die attach
- Wire bonding
- Packaging materials *
- Package types (TQFP, MLF, COB)
- Thermal design *

Refer to:

G. Torelli e S. Donati, *“Tecnologie e Materiali per l'Elettronica”*,
Ed. CUSL



Packaging

Packaging is used to:

- Provide electrical connection between IC pads and PCB lines
- Mechanical and chemical protection from external agents
- Easier handling
- Thermal dissipation

PACKAGING PHASES

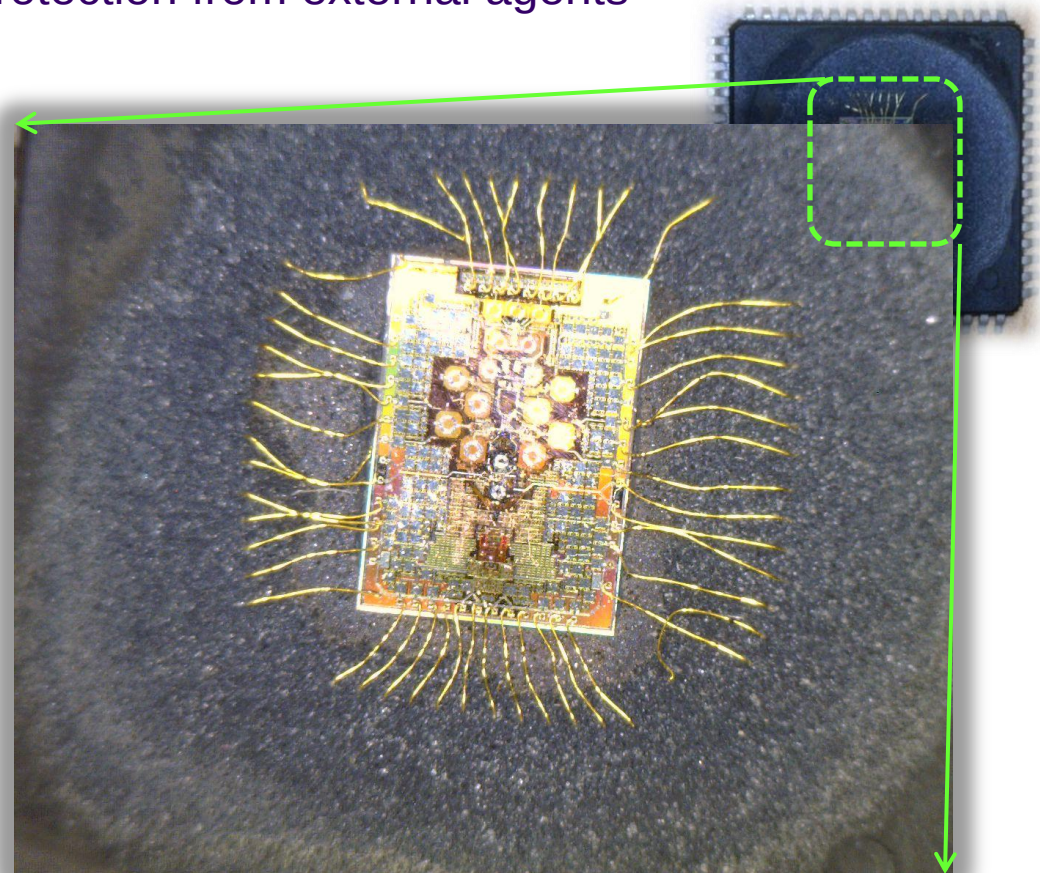
Die attach



Wire bonding



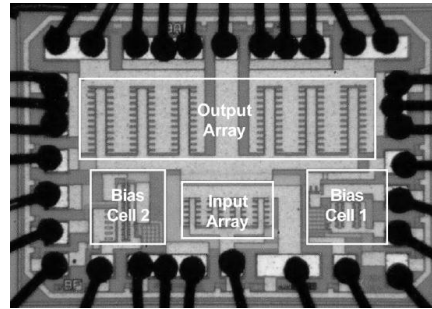
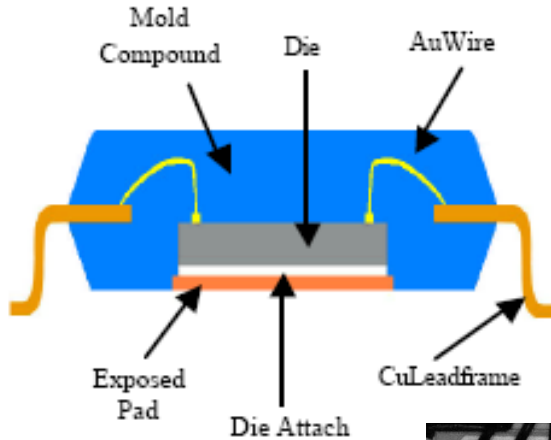
Sealing



Die attach

- **Eutectic solder:** wafer is back-plated with Au and package has an Au internal paddle. Eutectic Au/Si is formed at 400°C.
- **Sn/Pb solder:** wafer is back-plated and a tin/lead solution is deposited on the package paddle. Soldering is carried out at 200-350°C.
- **Conductive epoxy:** adhesive epoxy loaded with conductive materials (e.g. Au) is dispensed on the lead-frame. Soldering is carried out by means of epoxy polymerization at 125-175°C.

Wire Bonding



Manual bonding machine



Electrical parameters:

- Self Inductance $\sim 1\text{nH} / \text{mm}$
- DC resistance $\sim 30\text{m}\Omega / \text{mm}$
- Capacitance $\sim 100\text{fF} / \text{mm}$

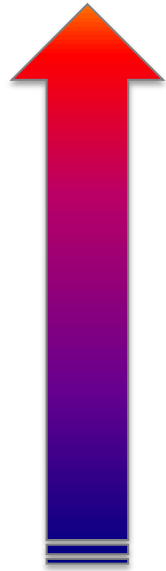
Wire materials:

Au, Al

Typical bonding wire diameter $\sim 30\mu\text{m}$

Packaging Materials

COST



- Metal packages: (kovar)
 - Used for high power and high reliability devices
 - Excellent thermal dissipation
 - EM shield
 - High cost
- Ceramic packages: (alumina)
 - E.g. glass-seal (“frit-seal”)
 - Good thermal dissipation
 - Intermediate cost
- Plastic packages: (epoxy)
 - Mechanic stress due to different thermal coefficients
 - Low thermal conductivity
 - Low cost



Plastic Materials

- Definition: **polymers** (long chains of atoms bonded to one another)
These chains are made up of many repeating molecular units, derived from monomers through a process called *polymerization*.
- Polymerization processes: polyaddition, direct polymerization and polycondensation
- Excellent isolation properties: strong bonds between monomers provide a high electric stiffness ($\bar{E}_{MAX}$)
- Mechanical properties can be improved using additives such as glass fibers

For plastic and ceramic materials, refer to:

Dispense di G. Torelli e S. Donati, “*Tecnologie e Materiali per l'Elettronica*”, Ed. CUSL

Plastic Materials

- **Thermoplastic materials**: teflon (PTFE), polystyrene, polycarbonates
 - Melt reversibly at high temperatures
 - Typically quite flexible
- **Thermosetting plastics**: epoxy resin, silicon resin, polyester, ...
 - Harden irreversibly after it is cured
- Applications:
 - Capacitors dielectric material (polystyrene, polyester resin, polycarbonates)
 - Printed circuit board (epoxy, teflon)
 - Isolation (teflon)
 - Packages (epoxy)

Relevant Parameters

- | | |
|--|------------------------------------|
| • Thermal conductivity [W/°C cm] | 0.1 - 0.3 |
| • Thermal capacity [J/°C cm ³] | 40 – 160 |
| • Resistivity [GΩ cm] | >1 |
| • Dielectric strength E _R [kV/mm] | 10 - 100 |
| • Loss tangent Tan δ (= – Im[ε] / Re[ε]) | 10 ⁻⁴ -10 ⁻² |

Ceramic Materials

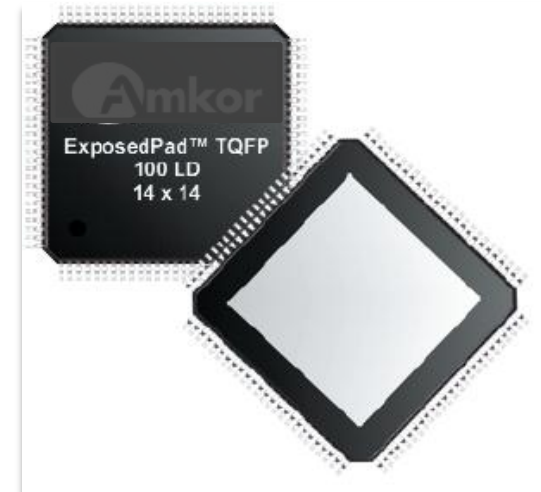
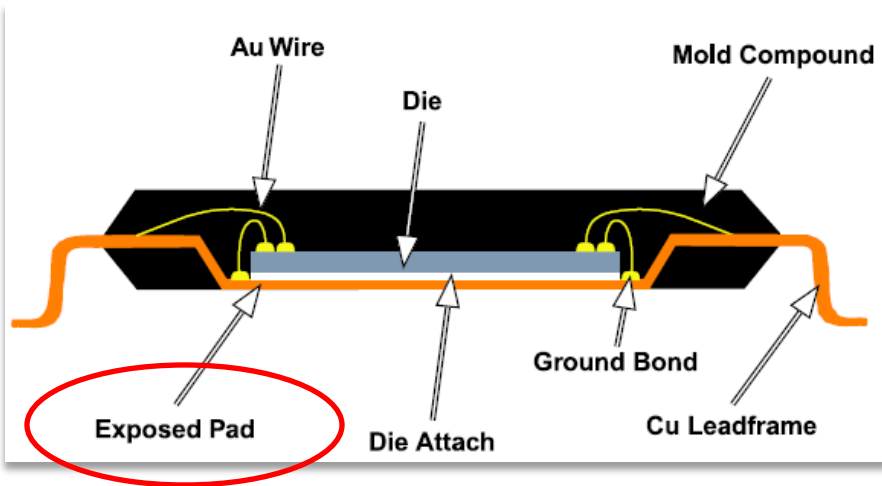
- Ceramic materials are compounds obtained from various materials reduced in fine particles, as a result of a *firing* (sinterization) process
- Features:
 - Hardness, stiffness
 - Immunity to humidity and corrosion
 - Good isolating and resistive materials can be synthesized

Production Process

- Grinding
 - Compound materials are reduced to fine particles ($\varnothing \sim 1\text{mm}$)
- Compact formation
 - Usually through mechanical pressure
- Firing
 - Liquid phase: sintering is carried out above the melting point of at least one component;
 - Solid phase: grain diffusion; better mechanical properties and reduced aging effects

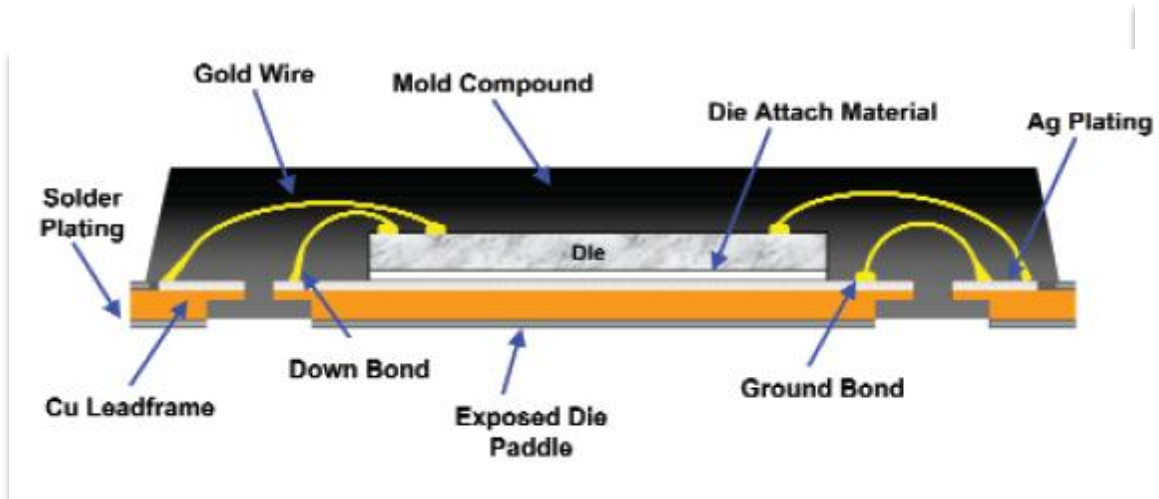
Exposed-Pad TQFP

Exposed Pad Thin Quad Flat Package (TQFP)



- The Exposed Pad can increase heat dissipation by as much as 110% over a standard TQFP.
- The Exposed Pad can be connected to ground, reducing “ground” inductance for high frequency applications.
- Used in high performing products such as telecom, disk drives, pagers, wireless, CATV/RF modules, radio and other similar applications.

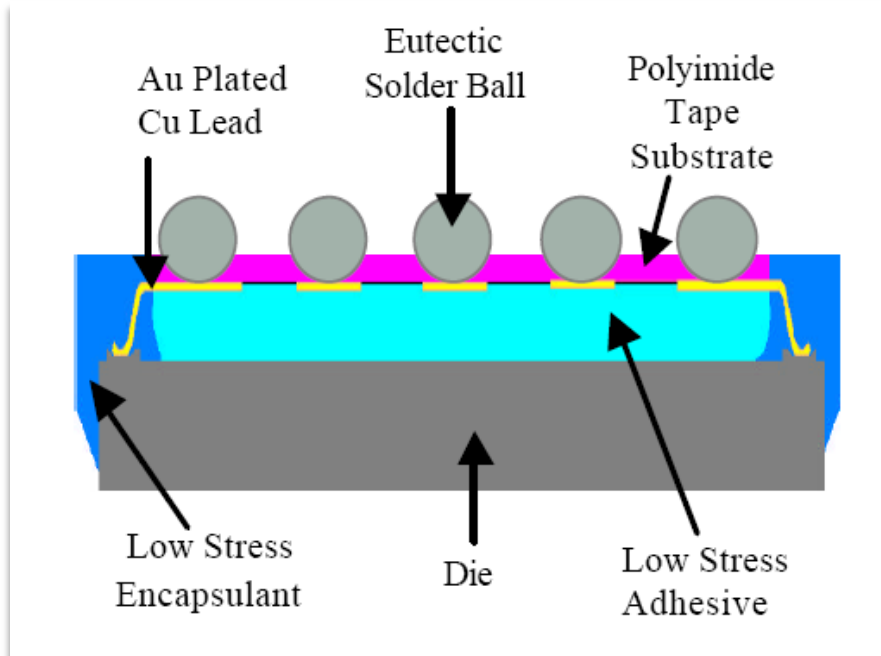
Exposed Pad Micro-Lead Frame



- Plastic encapsulated package with a copper leadframe substrate
- reduced lead size strongly reduces the parasitic inductances and capacitances
- An ideal choice for handheld portable applications such as cell phones and PDAs or any other application where size, weight and package performance are required issues.

Chip-Scale Packages

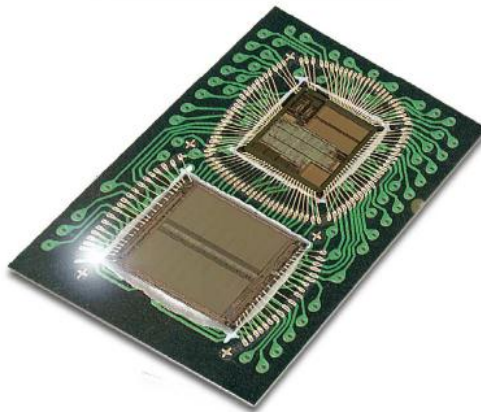
Ball Grid Array



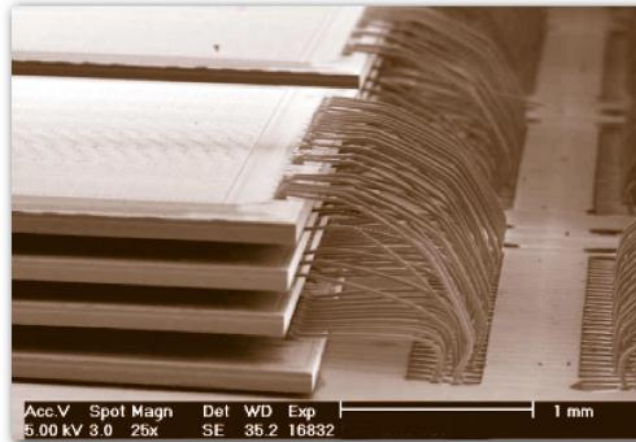
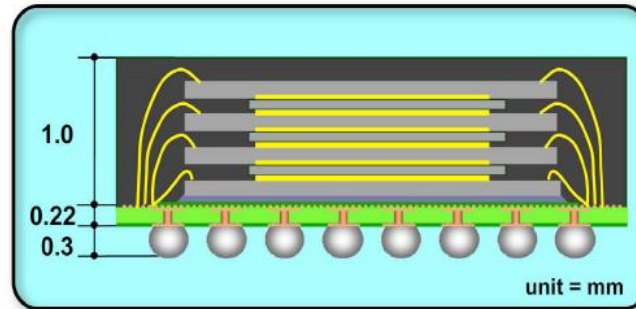
A true Chip Scale Package. Used for ICs with large pin count (e.g. memory, analog, ASICs, RF devices and simple PLDs requiring a small package size).

System-in-Package (SiP) Example

Multichip and Stacked Dice



Multichip Module

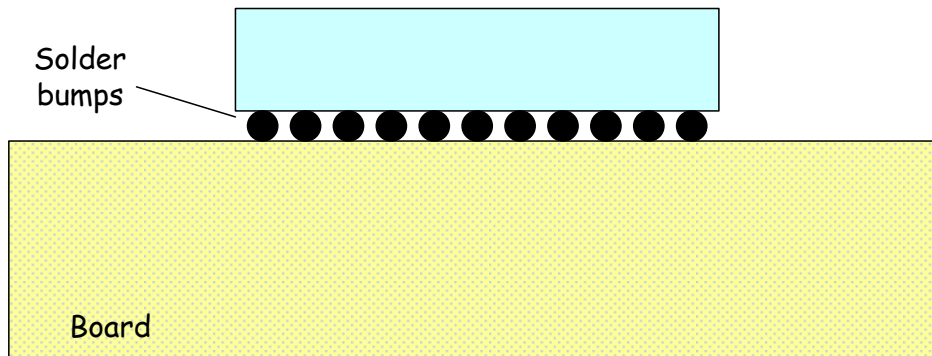


Stacked Dice

B. Murari, "Bridging the Gap Between the Digital and Real World: the Expanding Role of Analog Interface Technologies", International Solid-State Circuits Conference 2003, *San Francisco, February 10, 2003*

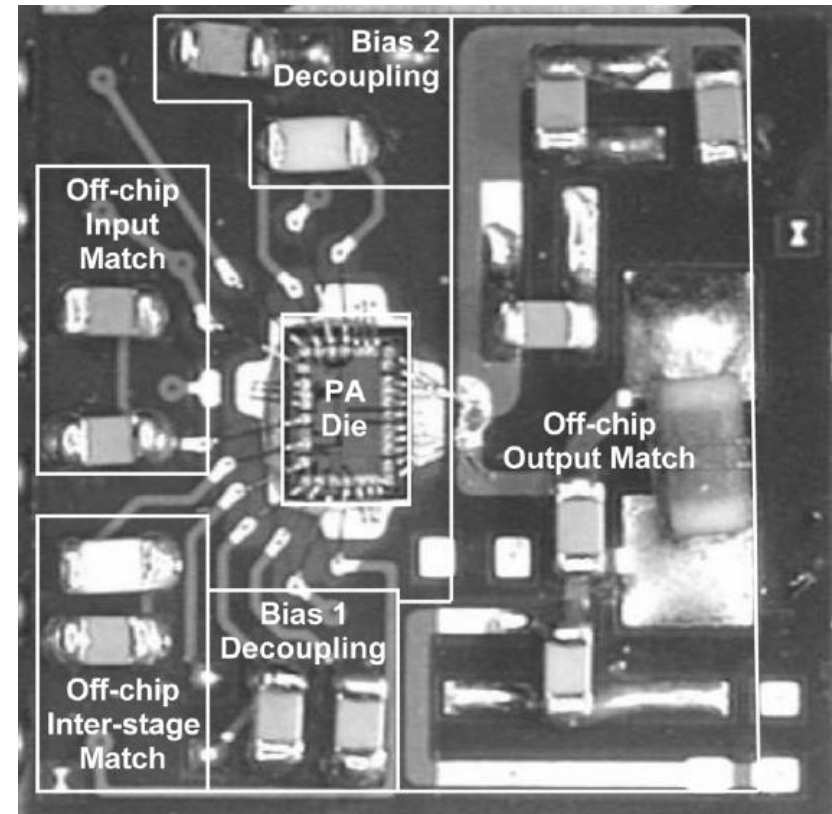
Chip-on-Board

Flip-chip



- Eliminate package parasitics
- Minimize size
- High speed / power applications

Chip-to-PCB wirebond



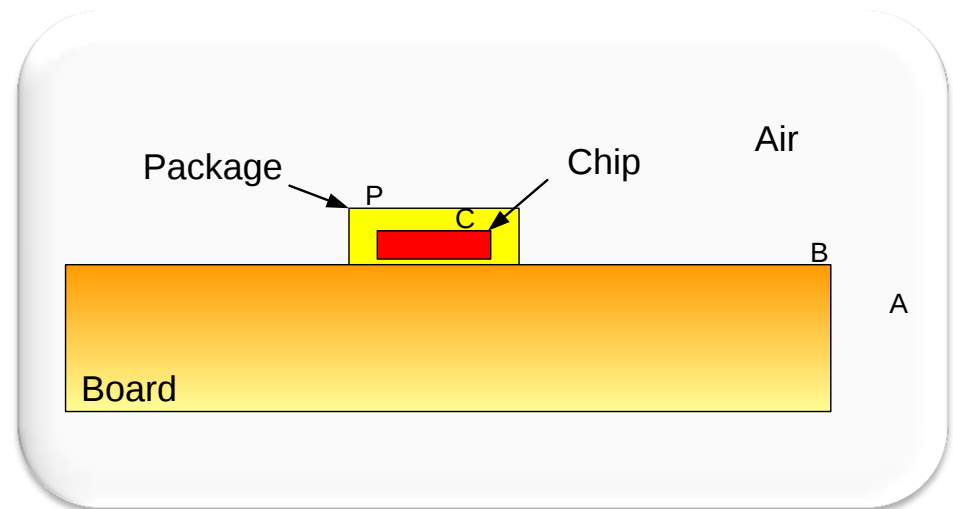
Thermal Design

- Temperature range:

- Commercial $0^{\circ}\text{C} < T < 70^{\circ}\text{C}$
- Industrial $-40^{\circ}\text{C} < T < 85^{\circ}\text{C}$
- Military range $-55^{\circ}\text{C} < T < 125^{\circ}\text{C}$

- Thermal exchange mechanisms:

- Conduction
- Convection
- Radiation



Electrical-Thermal Equivalent

Dissipated Power



Electrical Current

Temperature



Electrical Potential (Voltage)

Equivalent Thermal Resistance

$$R_{TH} = \frac{\Delta T}{P}$$



Electrical Resistance

$$R = \frac{\Delta V}{I}$$

Fourier Law

$$\Phi = -K \nabla T$$



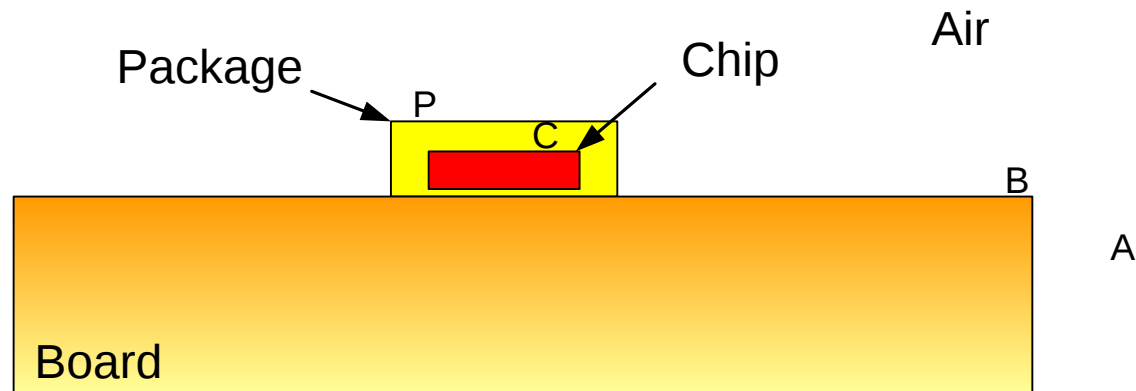
$$J = \sigma E = -\sigma \nabla V$$

K thermal conductivity [W/°Ccm]

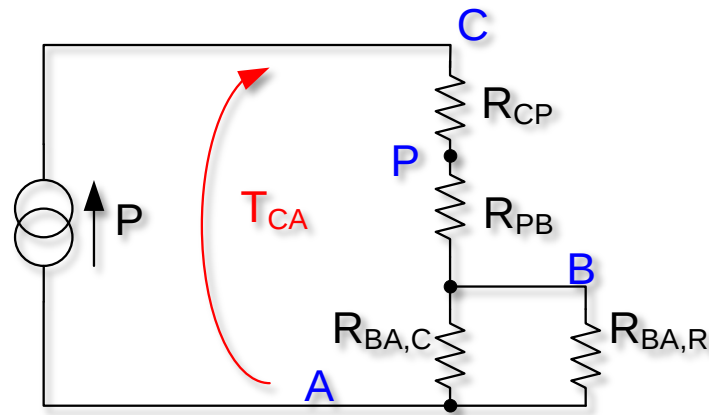


σ el. conductivity [S/cm]

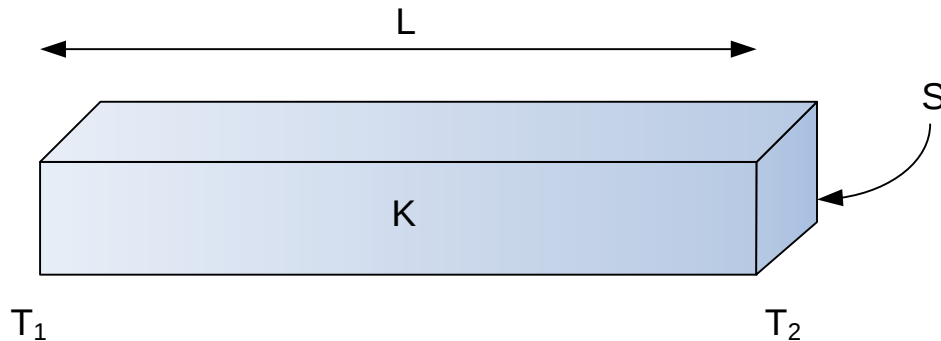
Thermal Modeling



Thermal Equivalent Circuit



Thermal Conduction



$$R_{TH} = \frac{1}{K} \frac{L}{S}$$

During transients *thermal capacitance* must be taken into account:

$$C_{TH} = \rho c L S$$

During transients thermal capacitance must be taken into account:

$$\frac{\partial T}{\partial t} = \frac{K}{\rho c} \frac{\partial^2 T}{\partial x^2} = \alpha \frac{\partial^2 T}{\partial x^2}$$

(Free) Thermal Convection

- The **Nusselt number** (N_{NU}) measures the enhancement of heat transfer from a surface that occurs in a 'real' situation, compared to the heat transferred if just conduction occurred.

$$N_{NU} = \frac{hL}{K}$$

Convection heat transfer coeff. $\rightarrow$ h
 Th. Conductivity $\rightarrow$ K
 Effective thermal conductivity $\rightarrow$ hL
 Characteristic length (Volume/Surface) $\rightarrow$ L

Convection thermal resistance:

$$R_{TH, CONV} = \frac{1}{hS}$$

Empirical expression:

$$h = 0.4 \left(\frac{\Delta T}{L} \right)^{1/4} \left[mW / ^\circ C cm^2 \right]$$

where ΔT is in $^\circ C$ and L in cm.

Thermal Radiation

- *Thermal radiation* is electromagnetic radiation emitted from the surface of an object which is due to the object's temperature. The total amount of radiation, of all frequencies, **goes up very fast as the temperature rises**:

$$P = \varepsilon \sigma S T^4$$

ε emissivity (<1)

σ Stefan-Boltzmann constant = $5.67 \cdot 10^{-8} \text{ W/m}^2\text{K}^4$

S surface area

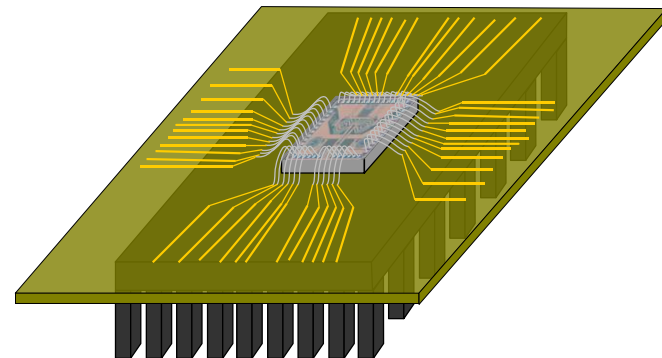
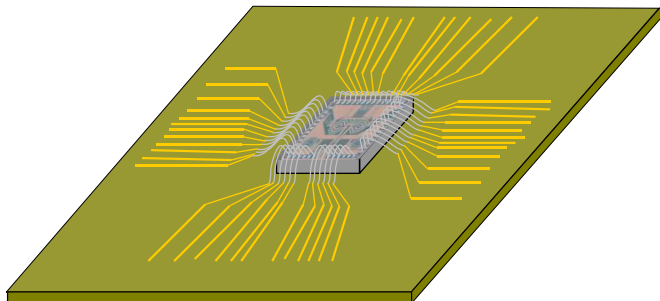
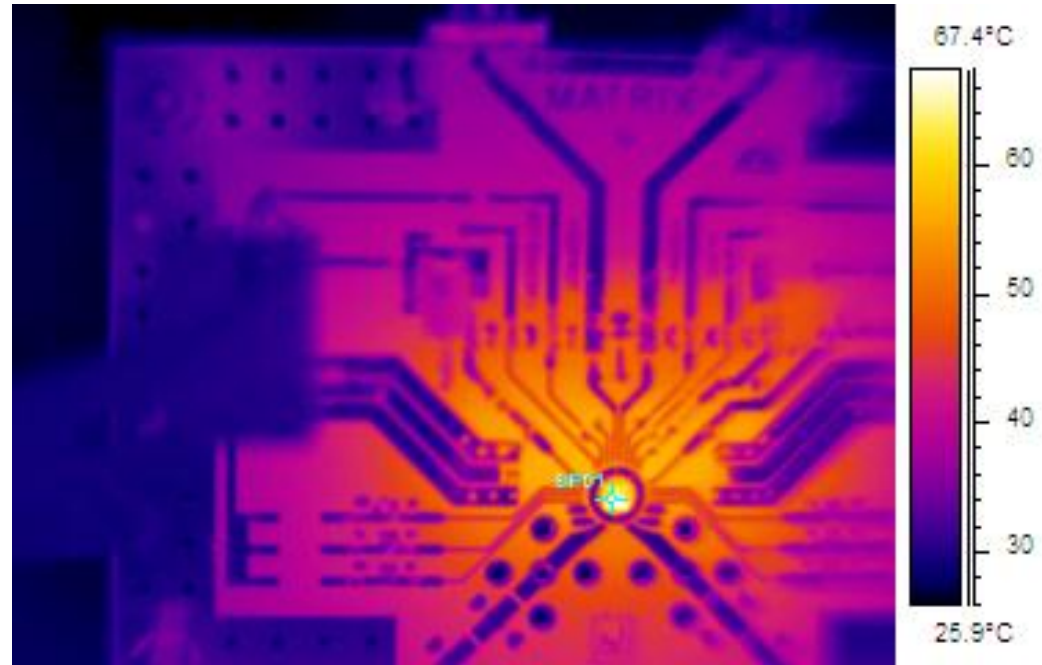
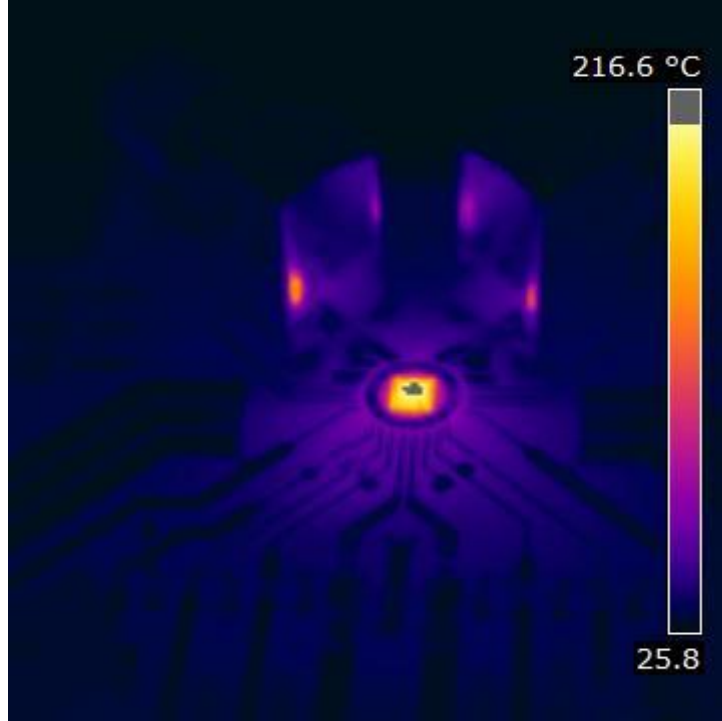
Power radiated toward ambient:

$$\Delta P \approx 4\sigma S T_a^3 \Delta T$$

Radiated Thermal Resistance:

$$R_{TH,R} \approx \frac{1}{4\sigma S T_a^3}$$

Thermal Diagram



Homework

10 devices over an 8cm x 12.5cm printed circuit board.

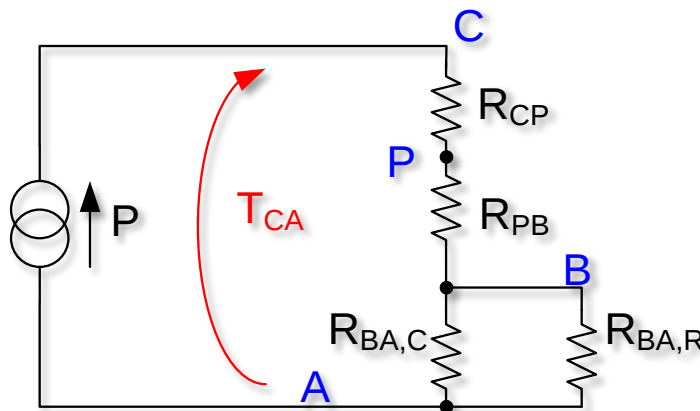
$$R_{CP}=20^{\circ}\text{C/W}$$

$$R_{PB}=3^{\circ}\text{C/W}$$

Maximum ambient temperature: 40°C

Maximum operating temperature of each device: 85°C

Find the maximum power dissipated by each element.



References

- References:

- www.amkor.com

- Reading Material:

- Dispense di G. Torelli. Introduzione alla tecnologia dei circuiti integrati su silicio. 2006. (IC Technologies)
- Dispense di G. Torelli e S. Donati, “*Tecnologie e Materiali per l'Elettronica*”, Ed. CUSL
- Dispense del corso *Microfabrication Technology*, UCB
<http://organics.eecs.berkeley.edu/~viveks/ee143/>